

TOSHIBA DIODE SILICON EPITAXIAL SCHOTTKY BARRIER TYPE

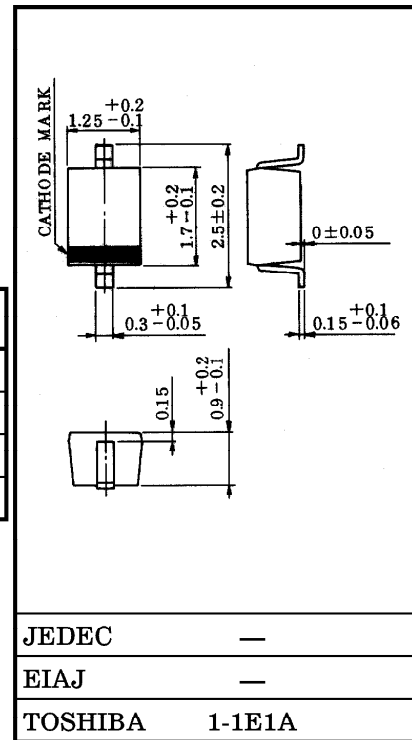
1SS315

UHF BAND MIXER APPLICATIONS.

Unit in mm

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Maximum (Peak) Reverse Voltage	V_{RM}	5	V
Forward Current	I_F	30	mA
Junction Temperature	T_j	125	°C
Storage Temperature Range	T_{stg}	-55~125	°C

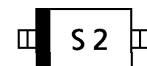


Weight : 0.004g

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Forward Voltage	V_F	$I_F = 2mA$	—	0.25	—	V
Forward Current	I_F	$V_F = 0.5V$	30	—	—	mA
Reverse Current	I_R	$V_R = 0.5V$	—	—	25	μA
Total Capacitance	C_T	$V_R = 0.2V, f = 1MHz$	—	0.6	—	pF

Marking



961001EAA2

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